L Number	Hits	Search Text	DB	Time stamp
1	3321	((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05 19:14
_	3321	(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/363) or (257/370) or (257/373)).CCLS.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	119	(((257/168) or (257/173) or (257/355) or	USPĀT;	2002/11/05 19:15
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or evenly	DERWENT;	
		or uniform or even) near12 (distribution	IBM_TDB	
3	60	or distributed)	HCDAT.	2002/11/05 10:10
٦	60	(((257/168) or (257/173) or (257/355) or (257/360) or (257/361) or (257/362) or	USPAT; US-PGPUB;	2002/11/05 19:19
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or evenly	DERWENT;	
		or uniform or even) near12 (distribution	IBM TDB	
		or distributed) and (esd or electrostatic	_	
		adj discharge)		
4	44	_ , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/11/05 19:22
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or evenly	DERWENT;	
		or uniform or even) near12 (distribution	IBM_TDB	
		or distributed) and (esd or electrostatic		
		adj discharge) and (resistor or	1	
		resistance) near15 (transistor or fet or mis or mos or mosfet or misfet or igfet or		
		jfet or dmos or dmosfet or cmos or		
	.	cmosfet)		
_	92	(257/168).CCLS.	USPAT;	2002/02/05 17:40
			US-PGPUB;	
			EPO; JPO;	
!			DERWENT;	
			IBM_TDB	
-	312	(257/173).CCLS.	USPAT;	2002/02/05 20:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	9	(("257/168").CCLS.) and	USPAT;	2002/02/05 20:15
		(("257/173").CCLS.)	US-PGPUB;	2302,02,03 20.13
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	plurality adj2 bipolar adj transistor.clm.	USPAT;	2002/02/05 20:16
		and esd	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	ا مرا	///#257/160#\\ CCTC \\	IBM_TDB	2002/02/05 00 15
-	36		USPAT;	2002/02/05 20:17
		(("257/173").CCLS.)) and esd and bipolar adj transistor	US-PGPUB; EPO; JPO;	
		auj clansiscoi	DERWENT;	
			IBM TDB	1
_	40	(plurality adj2 bipolar adj	USPAT;	2002/02/05 20:22
	"	transistor.clm. and esd) or	US-PGPUB;	, 52, 00 20.22
		(((("257/168").CCLS.) or	EPO; JPO;	1
		(("257/173").CCLS.)) and esd and bipolar	DERWENT;	
		adj transistor)	IBM TDB	
- !	547	resistor and esd and bipolar adj	USPAT;	2002/02/05 20:23
		transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	117	resistor and esd and ((parallel or	USPAT;	2002/02/05 20:34
		lateral\$2) near3 bipolar adj transistor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	İ
_	152	charpentier.in.	EPO	2002/02/05 20:35

_	395	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:57
-	166	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:43
_	97	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:47
-	94	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:48
	94	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:51
	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:51
_	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab. and (ic or integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:52
	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab. and (ic or integrated adj circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:54
	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab. and (ic or integrated adj circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:54
-	31	((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:57
_	20	(((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:57

[ <b>-</b>	16		USPAT;	2002/02/06 09:14
		(("257/173").CCLS.)) and esd adj	US-PGPUB;	
		protect\$3.ti,ab.) and bipolar adj2	EPO; JPO;	
		transistor) and resist\$3	DERWENT;	
	,	E042702	IBM_TDB	2002/02/06 00:16
-	3	5043782.pn.	USPAT; US-PGPUB;	2002/02/06 09:16
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	5708550.pn.	USPAT;	2002/02/06 09:15
-		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-61292351\$-\$.did.	USPAT;	2002/02/06 09:16
	1		US-PGPUB;	
	İ		EPO; JPO;	
			DERWENT;	
	395	((257/168) or (257/173)).CCLS.	IBM TDB	2002/02/06 11-27
-	393	((237/100) OL (237/173)).CCL3.	USPAT; US-PGPUB;	2002/02/06 11:37
1	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	("L3 and esd adj2 protection.ti,ab.").PN.	USPAT;	2002/02/06 10:58
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	29	' '	USPAT;	2002/02/06 10:58
	-	esd adj2 protection.ti,ab.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
l _	7	///"257/169"\ or /"257/172"\\ CCIC \ and	IBM_TDB	2002/02/06 10:50
_	·	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and	USPAT; US-PGPUB;	2002/02/06 10:59
		bipolar.ti,ab.	EPO; JPO;	
		Dipolar. Cr, ab.	DERWENT;	
			IBM TDB	
-	0	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 10:59
		esd adj2 protection.ti,ab. and	US-PGPUB;	
		bipolar.ti,ab. and plurality adj2 bipolar	EPO; JPO;	
			DERWENT;	
		444,000,000	IBM_TDB	
-	0	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 11:00
		esd adj2 protection.ti,ab. and	US-PGPUB;	
		bipolar.ti,ab. and plurality adj2 transistor	EPO; JPO;	
		CLANSISCOL	DERWENT; IBM TDB	
_	15	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 11:00
	13	esd adj2 protection.ti,ab. and bipolar adj	US-PGPUB;	2002/02/00 11:00
		transistor	EPO; JPO;	ļ
			DERWENT;	
			IBM TDB	
_	12	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 11:02
		esd adj2 protection.ti,ab. and bipolar adj	US-PGPUB;	
		transistor and resist\$3	EPO; JPO;	
	İ		DERWENT;	
	ا _ ا	/// (8057/1608) /8057/1708:	IBM_TDB	0000465455
-	5	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 11:02
		esd adj2 protection.ti,ab. and bipolar adj	US-PGPUB;	
		transistor and resist\$3 and parallel	EPO; JPO;	
			DERWENT;	
_	3	((("257/168") or ("257/173")).CCLS.) and	IBM_TDB USPAT;	2002/02/06 11:48
		esd adj protection.ti,ab. and bipolar adj	US-PGPUB;	2002/02/00 11:48
		transistor.ti,ab.	EPO; JPO;	
		• • •	DERWENT;	
			IBM TDB	
		· · · · · · · · · · · · · · · · · · ·	·	

-	131	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 11:49
			DERWENT;	
_	1	transistor.ti,ab. and plurality adj2	IBM_TDB USPAT; US-PGPUB;	2002/02/06 14:06
		(bipolar or transistor) and resist\$3 and parallel	EPO; JPO; DERWENT; IBM TDB	
-	12	or purpose) near10 \$3bipolar adj	USPĀT; US-PGPUB;	2002/02/06 14:08
		transistor)	EPO; JPO; DERWENT; IBM TDB	
_	1	("0708550").PN.	USPĀT; US-PGPUB;	2002/02/06 15:07
•			EPO; JPO; DERWENT; IBM TDB	
-	2	("5708550").PN.	USPAT; US-PGPUB; EPO; JPO;	2002/02/06 15:35
			DERWENT; IBM_TDB	
_	7	(("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.	USPĀT	2002/02/06 15:20
_	5	((("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404")	USPAT; US-PGPUB;	2002/02/06 15:21
		or ("5623387") or ("5272371")).PN.) and (base adj region and bipolar adj transistor)	EPO; JPO; DERWENT; IBM TDB	
_	0	("esd adj protection.ti,ab and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 15:35
_	0	("esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path").PN.	IBM_TDB USPAT; US-PGPUB;	2002/02/06 15:36
			EPO; JPO; DERWENT; IBM TDB	
-	48	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 15:38
_	17	esd adj protection.ti,ab. and bipolar adj	IBM_TDB USPAT;	2002/02/06 15:40
		transistor.ti,ab. and current adj path	US-PGPUB; EPO; JPO; DERWENT;	
_	15		IBM_TDB USPAT;	2002/02/06 16:49
		protection and (increase near12 path)	US-PGPUB; EPO; JPO; DERWENT;	
_	12	bipolar adj transistor and esd adj protection and ((base near10 (surround\$3	IBM_TDB USPAT; US-PGPUB;	2002/02/06 17:01
		or enclos\$3)) near10 (emitter or collector))	EPO; JPO; DERWENT;	
_	710	near10 (surround\$3 or enclos\$3)) near10	IBM_TDB USPAT; US-PGPUB;	2002/02/06 17:04
		(emitter or collector))	EPO; JPO; DERWENT; IBM TDB	
				· · · · · · · · · · · · · · · · · · ·

_	506	near5 (surround\$3 or enclos\$3)) near5	USPAT; US-PGPUB;	2002/02/06 17:05
		(emitter or collector))	EPO; JPO; DERWENT;	
	224		IBM_TDB	2002/02/06 17:05
-	334	bipolar adj transistor.ti,ab. and ((base near3 (surround\$3 or enclos\$3)) near3	USPAT; US-PGPUB;	2002/02/06 17:05
		(emitter or collector))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000 (00 (05 17 07
-	2	bipolar adj transistor.ti,ab. and ((base near3 (surround\$3 or enclos\$3)) near3	USPAT; US-PGPUB;	2002/02/06 17:07
		(emitter or collector)) and esd.ti,ab. and	EPO; JPO;	
		protection.ti,ab.	DERWENT;	
<u>.</u>			IBM_TDB	
-	5	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06 17:10
		near4 (surround\$3 or enclos\$3)) near4 (emitter or collector)) and (electrostatic	US-PGPUB; EPO; JPO;	
		adj discharge or esd).ti,ab. and	DERWENT;	
		protection.ti,ab.	IBM_TDB	
-	430	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06 17:11
		near4 (surround\$3 or enclos\$3)) near4 (emitter or collector))	US-PGPUB; EPO; JPO;	
		(emittel of collector)	DERWENT;	
			IBM TDB	
-	6	bipolar adj transistor.ti,ab. and ((base	USPĀT;	2002/02/06 17:32
		near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	
		(emitter or collector)) and (esd with protection)	EPO; JPO; DERWENT;	
		protection	IBM TDB	
-	997	(257/355).CCLS.	USPĀT;	2002/02/06 17:33
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	95		USPĀT;	2002/02/06 17:42
		and bipolar adj transistor	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	4		USPĀT;	2002/02/06 17:39
		<pre>protection and bipolar adj transistor) and ((base near7 (surround\$3 or enclos\$3))</pre>	US-PGPUB;	
		near7 (emitter or collector))	EPO; JPO; DERWENT;	
		(3	IBM TDB	
-	1115	((257/360) or (257/361) or (257/362) or	USPAT;	2002/02/06 17:38
		(257/363)).CCLS.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	122	((("257/360") or ("257/361") or	USPĀT;	2002/02/06 17:39
		("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor	US-PGPUB; EPO; JPO;	
		adj proceedion and priporar adj transistor	DERWENT;	
			IBM_TDB	
-	6		USPAT;	2002/02/06 17:42
		("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor)	US-PGPUB; EPO; JPO;	
		and ((base near7 (surround\$3 or enclos\$3))	DERWENT;	
		near7 (emitter or collector))	IBM_TDB	
-	893	((257/370) or (257/373)).CCLS.	USPAT;	2002/02/06 17:41
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	7	((( == ), = ) = ( == ), = = ), = = = ;	USPAT;	2002/02/06 17:42
		esd adj protection and bipolar adj transistor	US-PGPUB; EPO; JPO;	
		· · · · · · · · · · · · · · · · · · ·	DERWENT;	
			IBM_TDB	

-	0		USPAT;	2002/02/06 18:25
	1	esd adj protection and bipolar adj	US-PGPUB;	
		transistor) and ((base near7 (surround\$3	EPO; JPO;	
	1	or enclos\$3)) near7 (emitter or	DERWENT;	
		collector))	IBM TDB	
_	192	bipolar adj transistor.ti,ab. and second	USPAT;	2002/02/06 18:28
		adj2 well	US-PGPUB;	
		···· <b>,</b> - ····	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	65	bipolar adj transistor.ti. and second adj2	USPAT;	2002/02/06 18:42
		well	US-PGPUB;	2002/02/00 10:42
		Well	EPO; JPO;	
			DERWENT;	
			1	
			IBM_TDB	0000/00/06 10 45
- ,	2		USPAT;	2002/02/06 18:45
		second adj2 well	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	15	lateral adj bipolar adj transistor.ti,ab.	USPĀT;	2002/02/06 18:45
		and second adj2 well	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	(source or drain) adj regions same	USPAT;	2002/02/07 08:33
		through-contact\$3	US-PGPUB;	2002, 02, 01
		chiough concuces	EPO; JPO;	Ì
			DERWENT;	
			· ·	
	2	formed adj2 "same substrate" same	IBM_TDB USPAT;	2002/02/07 10:01
_	3		1	2002/02/0/ 10:01
	1	plurality adj2 bipolar adj transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	((	USPAT	2002/02/07 10:02
		or ("6277689")).PN.		
-	0	jp-0361292351\$-\$.did.	USPAT;	2002/02/07 10:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	jp-361292351\$-\$.did.	USPAT;	2002/02/07 10:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
! _	2	jp-61292351\$-\$.did.	USPAT;	2002/02/07 10:04
		]		2002/02/07 10:04
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L	<u> </u>		IBM_TDB	